

Silicon epitaxial planer type

For general purpose

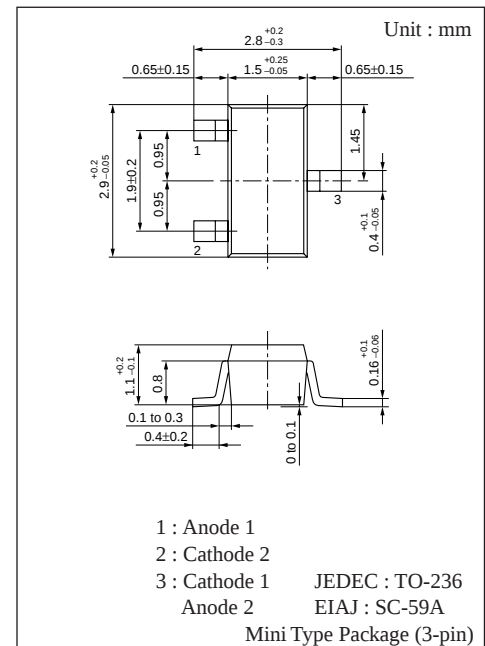
■ Features

- Two elements incorporated in one package, enabling high-density mounting
- Soft recovery characteristic (t_{rr} : 100ns)
- Series connection

■ Absolute Maximum Ratings (Ta= 25°C)

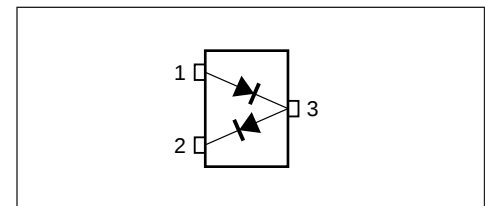
Parameter		Symbol	Rating	Unit
Reverse voltage (DC)		V_R	40	V
Repetitive peak reverse voltage		V_{RRM}	40	V
Average forward current	Single	$I_F (AV)$	100	mA
	Series		75	
Repetitive peak forward current	Single	I_{FRM}	225	mA
	Series		170	
Non-repetitive peak forward surge current	Single	I_{FSM}^*	500	mA
	Series		325	
Junction temperature		T_j	150	$^{\circ}C$
Storage temperature		T_{stg}	- 55 to +150	$^{\circ}C$

* t=1s



Marking Symbol : M2F

■ Internal Connection

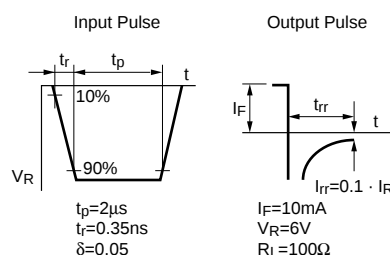
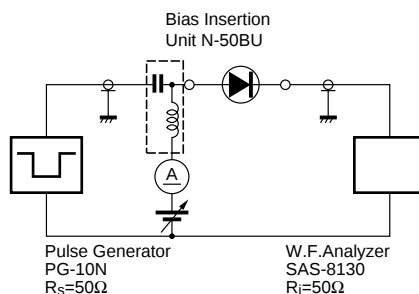


■ Electrical Characteristics (Ta= 25°C)

Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	$V_R = 40V$			10	nA
Forward voltage (DC)	V_{F1}	$I_F = 100\mu A$	0.65		0.72	V
	V_{F2}	$I_F = 100mA$			1.2	V
Terminal capacitance	C_t	$V_R = 6V, f = 1MHz$		1	2	pF
Reverse recovery time	t_{rr}^*	$I_F = 10mA, V_R = 6V$ $I_{rr} = 0.1 \cdot I_R, R_L = 100\Omega$			100	ns

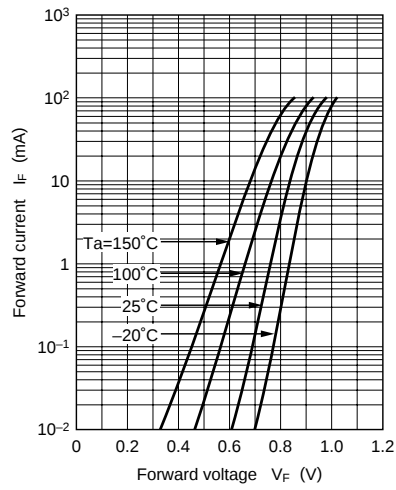
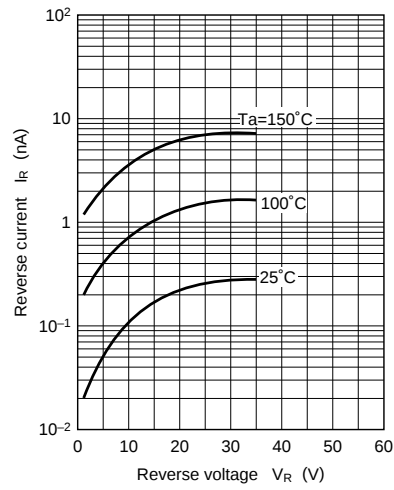
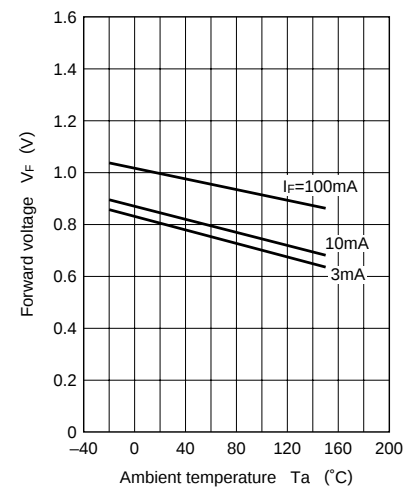
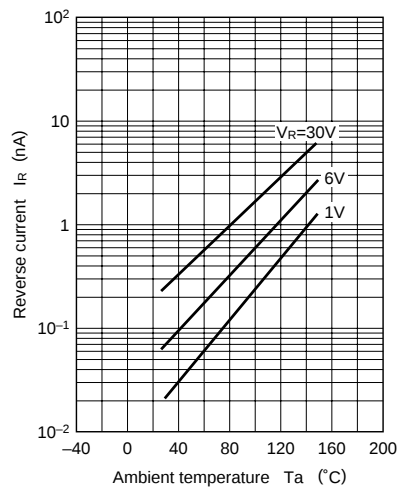
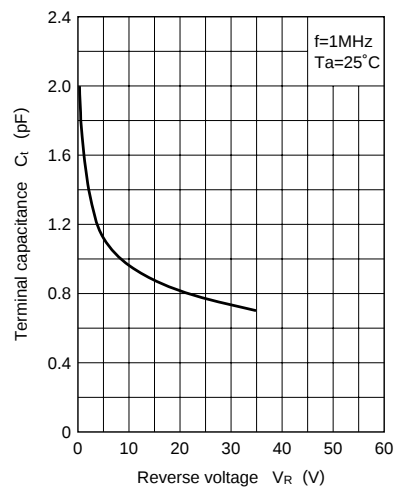
Note 1 : Rated input/output frequency : 10MHz

2 : * t_{π} measuring circuit



■ Marking



$I_F - V_F$  $I_R - V_R$  $V_F - T_a$  $I_R - T_a$  $C_t - V_R$  $I_F(\text{surge}) - t_w$ 